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	COMPLETE IF KNOWN		
Application Number	10/642,370		
Confirmation Number	2543		
Filing Date	08/15/2003		
First Named Inventor	Man Wang		
Group Art Unit	2819		
Examiner Name			
Attorney Docket No.	384848008US		

				U.S. PATENT DOCUMENTS		
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*EXAMINER:	Initial if reference considered, whether or not criteria is in conformal	nce with MPEP 609. Draw line through citation if not in conformance and not
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Dril D. Clay	DATE CONSIDERED 2/1/05
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